| Ref # | Hits | Search Query | DBs | Default Operator | . Plurals | Time Stamp |
|-----------|-------|---|---|---------------------|-----------|------------------|
| S1 | 16352 | "MOCVD" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:22 |
| S2 | 409 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:36 |
| S3 | 0 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:37 |
| S4 | 299 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:37 |
| S5 | 7 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:37 |
| S6 | 7 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:38 |
| S7 | 2 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and angle and gradient and grow\$4 and buffer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:51 |
| S8 | 130 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:52 |

| S9 | 76 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 holder or support) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:53 |
|-----|--------|---|---|----|----|------------------|
| S10 | 39 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:53 |
| S11 | 29 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:54 |
| S12 | 25 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:56 |
| S13 | 0 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and gradient | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:54 |
| S14 | 882909 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle buffer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 11:56 |
| S15 | 6 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle and buffer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:07 |
| S16 | 25 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and direction and angle | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:08 |

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| S17 | 39 | (epitaxial near4 grow\$4) and "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:27 |
| S18 | 56 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON . | 2006/08/03 12:31 |
| S19 | 56 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:32 |
| S20 | 51 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow\$4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:36 |
| S21 | 17 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow\$4 and buffer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:39 |
| S22 | 9 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow\$4 and "InGaAs" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:41 |
| S23 | 2 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and (substrate near4 (holder or support)) and grow\$4 and "InGaAs" and "InAlAs" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/03 12:47 |
| S24 | 8 | "MOCVD" and (polish near8 (substrate or semiconductor or wafer)) and grow\$4 and "InGaAs" and "InAlAs" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR _y | ON | 2006/08/03 12:47 |

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| S25 | 6233 | "MOCVD" near8 (substrate or semiconductor or wafer) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR ' | ON | 2006/08/04 09:23 |
| S26 | 70 | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:23 |
| S27 | 0 | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 gradient) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:23 |
| S28 | 25 | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and angle | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:24 |
| S29 | 16 | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:24 |
| S30 | 5 | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:25 |
| S31 | | "MOCVD" near8 (substrate or semiconductor or wafer) and (polish near8 (substrate or semiconductor or wafer)) and (angle near8 (substrate or semiconductor or wafer)) and ((support or holder) near8 (substrate or semiconductor or wafer)) and grow\$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:27 |

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| S32 | 57541 | (epitaxial near4 grow\$4) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:27 |
| S33 | 2471828 | ((epitaxial near4 grow\$4) near8 semiconductor or substrate or wafer) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:28 |
| S34 | 33536 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:28 |
| S35 | 1837 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:29 |
| S36 | 0 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8 "MOCVD") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:29 |
| S37 | 41 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:30 |
| S38 | 20 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:37 |
| S39 | 0 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and arsenic | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:30 |

| S40 | 16 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:33 |
|-----|-------|---|---|----|------|------------------|
| S41 | 15 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:35 |
| S42 | 2 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and buffer and angle and direction and "InP" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:36 |
| S43 | 11 | "5494833" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON . | 2006/08/04 09:36 |
| S44 | 2 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and arsenic | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:38 |
| S45 | 9 | ((epitaxial near4 grow\$4) near8 (semiconductor or substrate or wafer)) and ("MOCVD" near8 (semiconductor or substrate or wafer)) and (polish near8(semiconductor or substrate or wafer)) and ("InGaAs" or "InAlAs") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:43 |
| S46 | 19224 | (semiconductor or substrate or wafer) near8 "InP" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:44 |

| S47 | 5061 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:45 |
|-------------|-------|---|--|------|------|------------------|
| S48 | 823 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow\$3) and "MOCVD" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:46 |
| S49 | 1 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow\$3) and "MOCVD" and (angle near4 gradient) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:47 |
| S50 | 134 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow\$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/08/04 09:48 |
| S51 | 97 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow\$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON . | 2006/08/04 09:48 |
| <u>\$52</u> | 21 | (semiconductor or substrate or wafer) near8 "InP" same ("InGaAs" or "InAlAs") and (epitaxial near4 grow\$3) and "MOCVD" and angle and (direction near8 (substrate or semiconductor or wafer)) and (crystal near4 (semiconductor or wafer or substrate)) and (density near4 (semiconductor or wafer or substrate)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR . | ON | 2007/04/17 08:01 |
| S53 | 44654 | (epitax\$4 near growth) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:02 |

| S54 | 10823 | (epitax\$4 near growth) and (substrate or wafer or carrier) near9 (support or holder or base) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:03 |
|-----|-------|--|--|------|----|------------------|
| S55 | 12321 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:03 |
| S56 | 1942 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:03 |
| S57 | 1203 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near9 (substrate or wafer or carrier or semiconductor)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:03 |
| S58 | 1145 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR - | ON | 2007/04/17 08:04 |
| S59 | 357 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:05 |

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|---------------------------------------|-----|--|--|----|------|------------------|
| S60 | 274 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:05 |
| S61 | 0 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and (angle near4 gradient) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:06 |
| S62 | 0 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and (angle near9 gradient) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:06 |
| S63 | 61 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 08:06 |
| S64 | 0 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and gradient | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON , | 2007/04/17 08:07 |

| S65 | 61 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 09:19 |
|-----|----|---|--|----|----|------------------|
| S66 | 0 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and (thick\$4 near9 ".05") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 09:20 |
| S67 | 0 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and (thickness near9 ".05") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 09:20 |
| S68 | 45 | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) near9 thick\$4 and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 09:27 |
| S69 | | (epitax\$4 near growth) and (substrate or wafer or carrier or semiconductor) near9 (support or holder or base) and MOCVD and (compound near4 (substrate or wafer or carrier or semiconductor)) near9 thick\$4 and (buffer near9 (substrate or wafer or carrier or semiconductor)) and arsenic and "InP" and angle and morphology | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/04/17 09:28 |

| S70 · | 0 | (epitax\$4 near growth) and | US-PGPUB; | OR | ON | 2007/04/17 09:28 |
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| | | (substrate or wafer or carrier or | USPAT; | | | |
| | | semiconductor) near9 (support or | USOCR; | | | |
| | | holder or base) and MOCVD and | FPRS; | | | |
| | | (compound near4 (substrate or | EPO; JPO; | | | |
| | | wafer or carrier or semiconductor)) | DERWENT; | | İ | |
| | | near9 thick\$4 and (buffer near9 | IBM_TDB | | | |
| | | (substrate or wafer or carrier or | | | | |
| | | semiconductor)) and arsenic and | | | | |
| | | "InP" and angle and morph\$4 | | | | |

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